

General Description

The CMSC012N06 is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. This device is well suited for use in compact DC/DC converter applications.

Features

- Low On-Resistance
- Low Gate Charge
- Surface Mount Package
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	20	A
$I_D@T_C=100^{\circ}C$		16	
I_{DM}	Pulsed Drain Current	60	A
EAS	Single Pulse Avalanche Energy ¹	45	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(Steady-State)	---	60	°C/W
$R_{\theta JC}$	Thermal Resistance Junction -Case(Steady-State)	---	2.5	°C/W

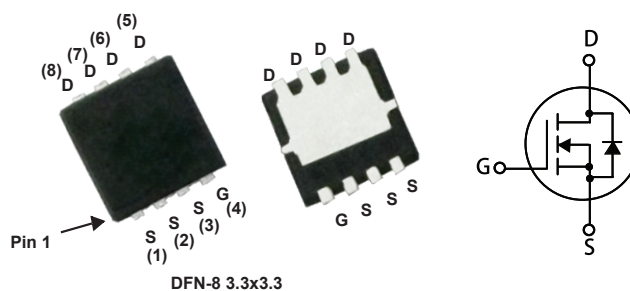
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
60V	11mΩ	20A

Applications

- High efficiency power supply
- Secondary synchronous rectifier

DFN-8 3.3x3.3 Pin Configuration



Type	Package	Marking
CMSC012N06	DFN-8 3.3x3.3	012N06

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	9.1	11	mΩ
		$V_{GS}=4.5V$, $I_D=15A$	---	15	17.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D = 250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 20V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	15	---	S
Q_g	Total Gate Charge	$V_{DS}=30V$, $I_D=20A$ $V_{GS}=10V$	---	15	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V$, $V_{GS}=10V$, $R_{GEN} = 3\Omega$ $I_D=20A$	---	11	---	ns
T_r	Rise Time		---	78	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	$V_{DS}= 30V$, $V_{GS}=0V$, $f=1MHz$	---	860	---	pF
C_{oss}	Output Capacitance		---	440	---	
C_{rss}	Reverse Transfer Capacitance		---	18	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	20	A
$I_{S,pulse}$	Diode pulse current		---	---	60	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=28A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Note :

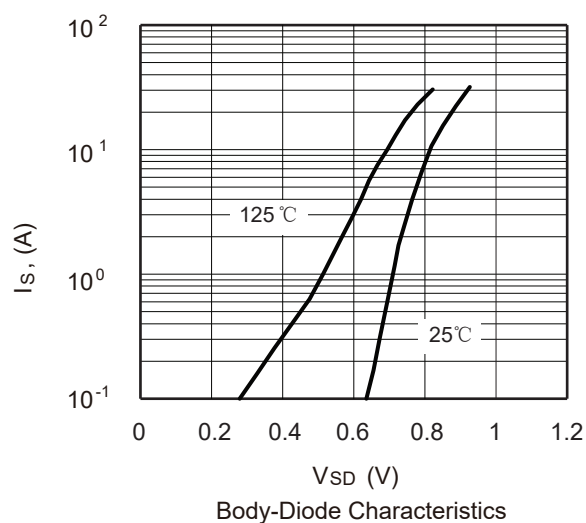
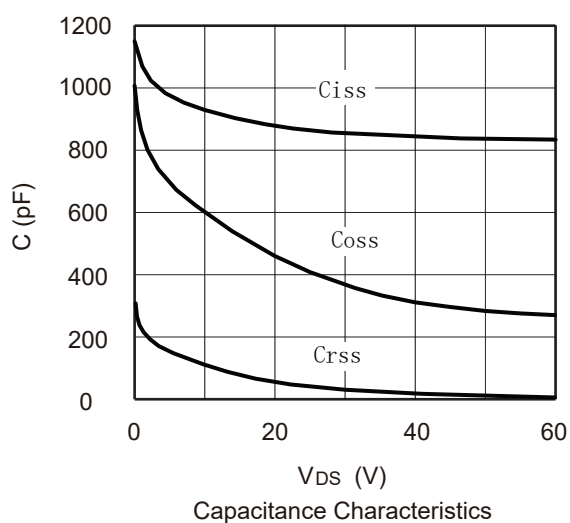
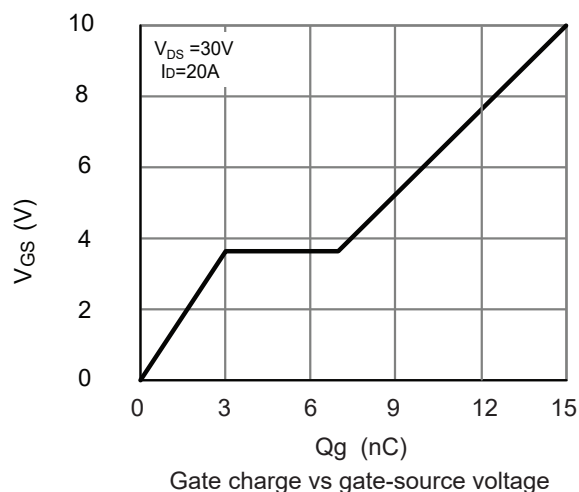
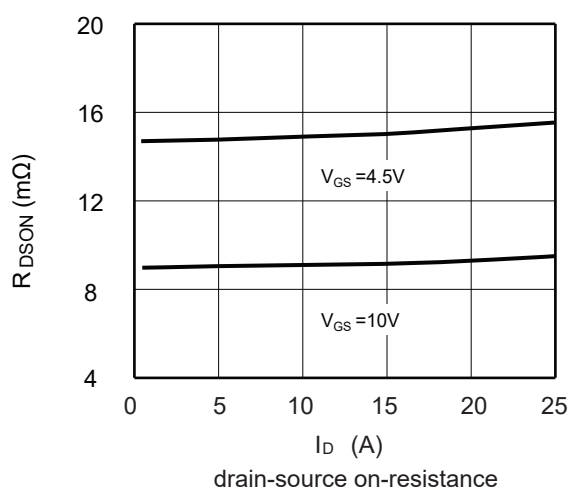
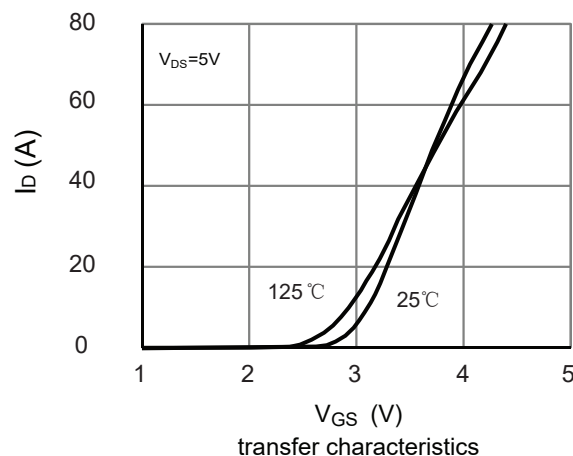
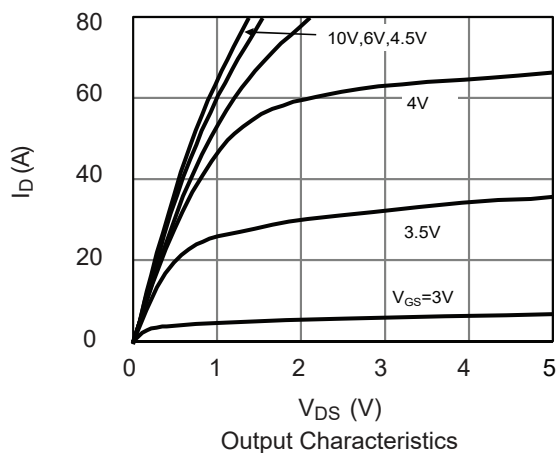
1.The EAS data shows Max. rating .The test condition is $V_{DS}=30V$, $V_{GS}=10V$, $L=0.5mH$, $I_{AS}=13.5A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

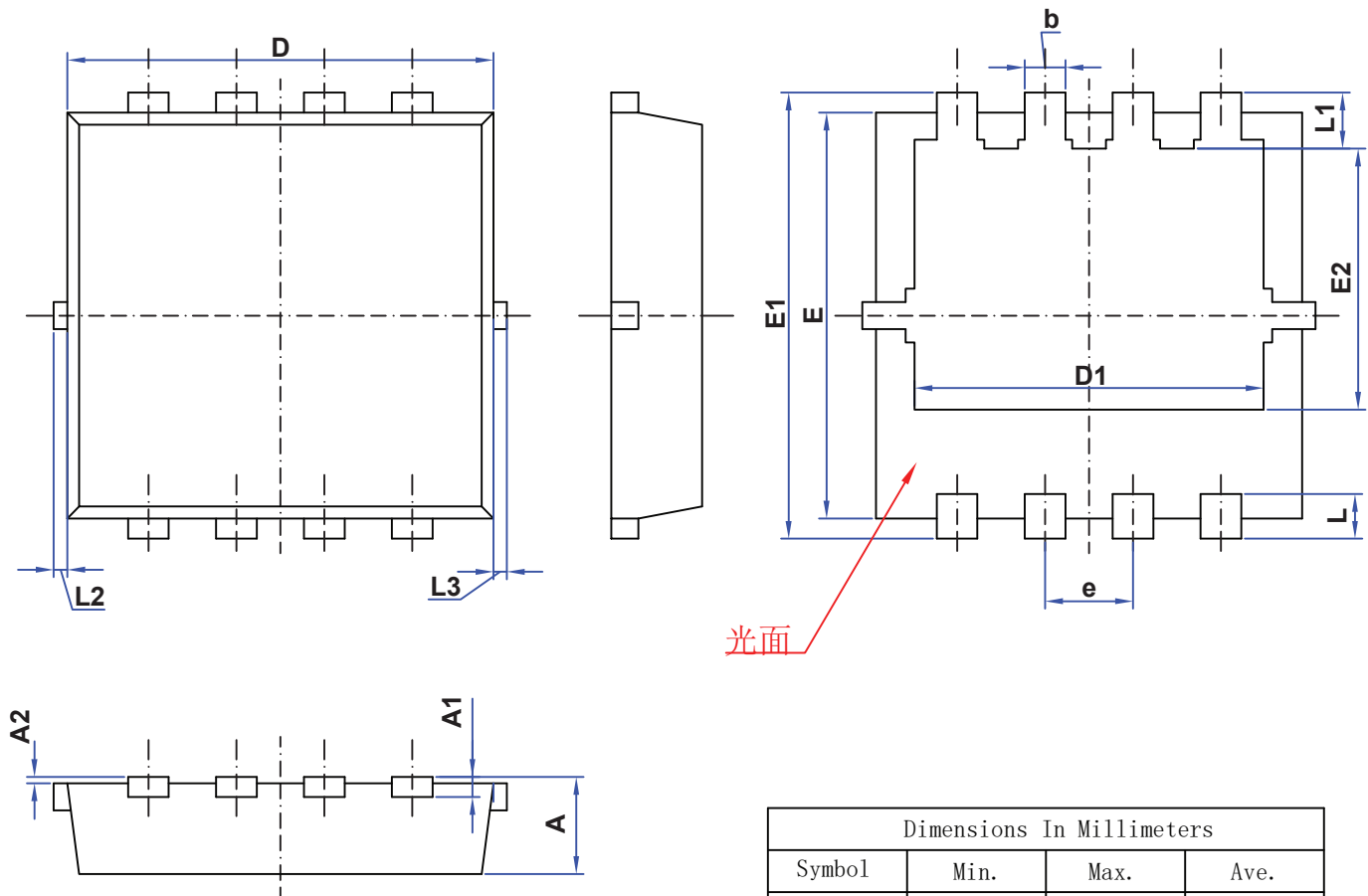
Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

Typical Characteristics



Package Dimension

DFN-8 3.3x3.3 Unit :mm



- 注:
1. 未注公差±0.10,
 2. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
 3. 标注单位mm

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.700	0.900	0.800
A1	0.100	0.200	0.150
A2	—	0.050	—
D	3.000	3.200	3.100
D1	2.350	2.550	2.450
E	3.000	3.200	3.100
E1	3.200	3.600	3.400
E2	1.635	1.835	1.735
b	0.200	0.400	0.300
e	0.550	0.750	0.650
L	0.250	0.650	0.450
L1	0.345	0.745	0.545
L2	0~0.100		
L3	0~0.100		